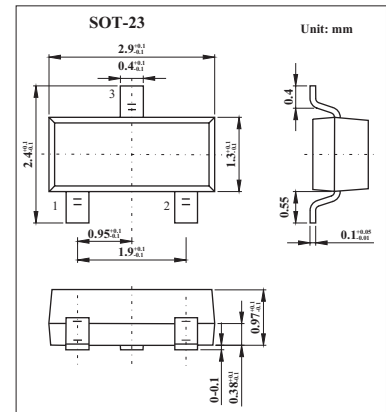


## Silicon Epitaxial Planar Diode

## HSM2692

## ■ Features

- Low forward resistance. ( $r_f = 0.9 \text{ max}$ )
- Low capacitance. ( $C = 1.2 \text{ pFmax}$ )
- MPAK package is suitable for high density surface mounting and high speed assembly.

■ Absolute Maximum Ratings  $T_a = 25^\circ\text{C}$ 

Parameter	Symbol	Value	Unit
Reverse Voltage	$V_R$	35	V
Power dissipation	$P_d$	150	mW
Junction temperature	$T_j$	125	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-45 to +125	$^\circ\text{C}$
Operation temperature	$T_{opr}$	-20 to +60	$^\circ\text{C}$

■ Electrical Characteristics  $T_a = 25^\circ\text{C}$ 

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Reverse voltage	$V_R$	$I_R = 10 \mu\text{A}$	35			V
Reverse current	$I_R$	$V_R = 25 \text{ V}$			50	nA
Forward voltage	$V_F$	$I_F = 10 \text{ mA}$			1.0	V
Capacitance	$C$	$V_R = 6 \text{ V}, f = 1 \text{ MHz}$			1.2	pF
Forward resistance	$r_f$	$I_F = 2 \text{ mA}, f = 100 \text{ MHz}$			0.9	$\Omega$

## ■ Marking

Marking	B1
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